

Amendments to the Specification:

Please replace paragraph beginning at line 23 of page 3 with the following amended paragraph:

-- As the exposure light has a shorter wavelength, its absorption remarkably increases in a material, and becomes incompatible with use a refraction element or lens for visible light and ultraviolet light. No glass material is compatible with a EUV light's wavelength, and a reflection-type or ~~cataoptric~~ catadioptric optical system is used which utilizes only a reflective element or multilayer mirror. A reticle also uses a cataoptric reticle that uses an absorber on a mirror to form a pattern to be transferred. --

Please replace paragraph beginning at line 26 of page 14 with the following amended paragraph:

-- The mask 120 is a cataoptric reticle, and forms, on a mirror, a circuit pattern (or image) to be transferred. The mask 120 is supported and driven by a mask stage 125. The diffracted light emitted from the mask 120 is projected onto the object 140 after reflected by the projection optical system 130. The mask 120 and object 140 are arranged optically conjugate with each other. Since the exposure apparatus 200 of this embodiment is a scanner, the mask 120 and object 140 are scanned to project a pattern on the mask 120, onto the ~~plate 230~~ object 140. --

Please replace paragraph beginning at line 10 of page 15 with the following amended paragraph:

--The mask stage 125 supports the mask 120 via a reticle chuck 125a, and is connected to a moving mechanism (not shown). The mask stage 125 can use any structure known in the art. The moving mechanism (not shown) includes a linear motor, etc., and moves the mask 120 by

driving the mask stage ~~25~~ 125 at least in a direction X. The exposure apparatus 100 scans the mask 120 and the object 140 synchronously. The reticle chuck 125a is an electrostatic chuck, and absorbs the mask 120 by an electrostatic absorbing force. The reticle chuck 125a forms a channel, similar to a mirror holder 132, which will be described later, and cooled by coolant supplied through the channel, such as water and nitrogen gas. The cooling structure to the mask 120 and the reticle chuck 125a quickly leads to the steady temperature. Here, X is a scan direction on the mask 120 or the object 140, Y is a direction perpendicular to it, and Z is a perpendicular direction on the surface of mask 120 or the object 140.--

Please replace the second full paragraph of page 20 (i.e., lines 11-17) with the following amended paragraph:

--The controller 230 controls driving by the drive mechanism ~~230~~ 220 so that the absorption member 210 absorbs the EUV light when the object 140 is not exposed. In other words, the controller 230 drives the absorption member 210 via the drive mechanism ~~230~~ 220 to the second position when the object 140 is exposed, and to the first position when the object is not exposed.
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Please replace paragraph beginning at line 18 of page 22 through line 3 of page 23 with the following amended paragraph:

--Referring now to FIG. 4, a description will be given of the incidence control mechanism 200A as a variation of the incidence control mechanism 200. FIG. 4 is a schematic structure of the incidence control structure 200A. The incidence control mechanism 200A includes, as shown in FIG. 4, the absorption member 210, a drive mechanism 220A, and a controller ~~230A~~ 230. The wafer stage 145 is configured to move the wafer chuck 145a to a position apart from the optical

path of the EUV light guided by the projection optical system 130. In other words, the wafer chuck 145a and the object 140 absorbed by the wafer chuck 145a can be moved from an image position of the projection optical system 130.--

Please replace two consecutive paragraphs beginning at line 3 of page 23 through line 2 of page 24 with the following amended paragraphs:

--The drive mechanism 220A is controlled by the controller ~~230A~~ 230, as described later, and moves the absorption member 210 to a position between the projection optical system 130 and the object 140 on the optical path of the exposure light (more specifically between the projection optical system 130's mirror 130a closest to the object 140 and the wafer chuck 145a) so that the absorption member 210 can absorb the EUV light when the object is not exposed. The drive mechanism 220A drives the absorption member 210 to a position of the wafer chuck 145a in the instant embodiment.

The controller ~~230A~~ 230 controls the wafer stage 145 so as to prevent the exposure light from entering the wafer chuck 145a when the object 140 is not exposed. The controller ~~230A~~ 230 controls driving by the drive mechanism 220A so that the absorption member 210 can absorb the EUV light when the object 140 is not exposed. In other words, the controller ~~230A~~ 230 drives the absorption member 210 via a moving mechanism of a wafer stage 145 to retreat the wafer stage 145 to a position apart from the optical path of the exposure light guided by the projection optical system 130, and to move the absorption member 210 via the drive mechanism 220 to a position on the optical path of the exposure light guided by the projection optical system 130.--

Please replace paragraph beginning at line 12 of page 25 through line 8 of page 26 with the following amended paragraph:

--Then, the controller 230 ~~or 230A~~ determined whether the optical elements in the illumination optical system 114, the mask 120, and the projection optical system 130 have a steady temperature distribution. The temperature distribution is a temperature difference between the center and the peripherals. The steady state is detected as discussed above. The controller 230 ~~or 230A~~ maintains the standby state, when determining that the optical element does not have the steady state, so as to prevent the temperature of the wafer chuck 145a from rising due to the EUV light. The controller 230 ~~or 230A~~ terminates the standby state when the optical element has the steady temperature distribution. Thus, the controller 230 ~~or 230A~~ removes the absorption member 210 in the incidence control mechanism 200 from the optical path of the EUV light or returning the wafer chuck 145a on the optical path of the EUV light for the incidence control mechanism 200A, and allows the EUV light to enter the object 140. The instant embodiment uses an arc or ring image surface to expose the entire surface of the mask 120 by scanning the mask 120 and the object 140 at speed ratio corresponding to a reduction ratio.--

Please replace paragraph beginning at line 25 of page 27 with the following amended paragraph:

--Referring to FIGs. 6 and 7, a description will now be given of an embodiment of a device fabricating method using the above mentioned exposure apparatus 100. ~~FIG. 12~~ FIG. 6 is a flowchart for explaining a fabrication of devices (*i.e.*, semiconductor chips such as IC and LSI, LCDs, CCDs, etc.). Here, a description will be given of a fabrication of a semiconductor chip as an example. Step 1 (circuit design) designs a semiconductor device circuit. Step 2 (mask

fabrication) forms a mask having a designed circuit pattern. Step 3 (wafer making) manufactures a wafer using materials such as silicon. Step 4 (wafer process), which is referred to as a pretreatment, forms actual circuitry on the wafer through photolithography using the mask and wafer. Step 5 (assembly), which is also referred to as a post-treatment, forms into a semiconductor chip the wafer formed in Step 4 and includes an assembly step (*e.g.*, dicing, bonding), a packaging step (chip sealing), and the like. Step 6 (inspection) performs various tests for the semiconductor device made in Step 5, such as a validity test and a durability test. Through these steps, a semiconductor device is finished and shipped (Step 7).--